

Title (en)
SEMICONDUCTOR COMPONENT COMPRISING DEFECT-RICH LAYER FOR OPTIMALLY CONTACTING EMITTERS, AND METHOD FOR THE PRODUCTION THEREOF

Title (de)
HALBLEITERBAUTEIL MIT DEFEKTREICHER SCHICHT ZUR OPTIMALEN KONTAKTIERUNG VON EMITTERN SOWIE VERFAHREN ZU DESSEN HERSTELLUNG

Title (fr)
COMPOSANT À SEMI-CONDUCTEUR COMPRENANT UNE COUCHE PRÉSENTANT DE NOMBREUX TROUS, POUR UNE MISE EN CONTACT OPTIMALE D'ÉMETTEURS, ET PROCÉDÉ PERMETTANT SA RÉALISATION

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Application
EP 11717511 A 20110505

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Abstract (en)
[origin: WO2011141142A1] The invention relates to a semiconductor component made of a semiconductor material, which component has a defect-rich semiconductor layer with a defect concentration of at least 103 defects per cm² disposed on a surface of the semiconductor component. The invention likewise relates to a method for producing said semiconductor component, a semiconductor layer being applied to the semiconductor material by means of physical or chemical vapor deposition and sintered in a further operating step, e.g., during or following vapor deposition. The desired defect concentration in the applied semiconductor layer is then set.

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See references of WO 2011141142A1

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